Abstract

A semiconductor device comprises a first insulating film, a wiring layer and a second insulating film formed in this order on a semiconductor substrate, the second insulating film being provided with one or more through holes formed onto the wiring layer, wherein the wiring layer is electrically isolated by the first insulating film and the second insulating film at a region other than a region where the through holes are formed, and a ratio between a total of a bottom area of the through holes formed onto the wiring layer and a top surface area of the wiring layer is 1:300 to 10,000.

This Sheet Has Been Replaced

